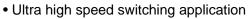
SILICON EPITAXIAL PLANAR DIODE

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Applications



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Average Forward Current	Ι _Ο	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Surge Current (10 ms)	I _{FSM}	2	A
Power Dissipation	P _{tot}	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at $V_R = 30 V$ at $V_R = 80 V$	I _R	0.1 0.5	μΑ
Total Capacitance at $V_R = 0$, f = 1 MHz	CT	3	pF
Reverse Recovery Time at $I_F = 10 \text{ mA}$	t _{rr}	4	ns



SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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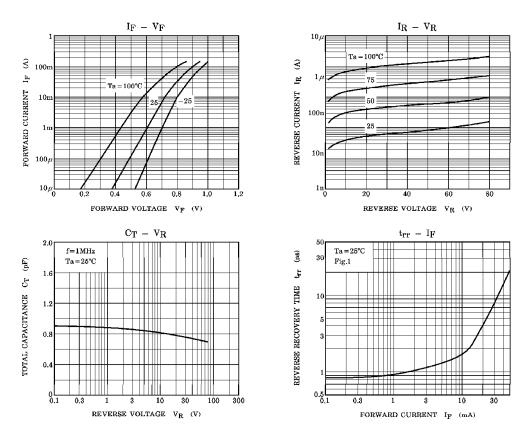
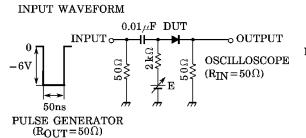
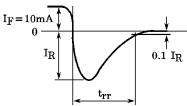


Fig.1 Reverse recovery time (t_{rr}) test circuit



OUTPUT WAVEFORM









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